

## Silicon NPN Power Transistors

2SC2739

## DESCRIPTION

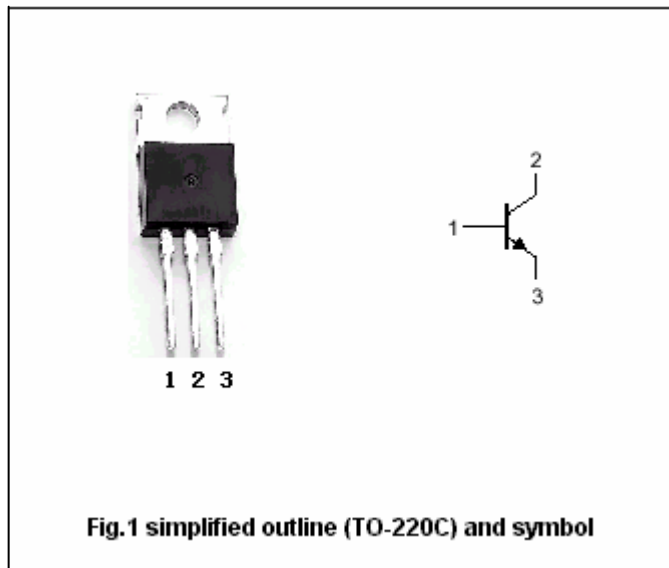
- With TO-220C package
- High speed switching
- High  $V_{CBO}$
- Low saturation voltage

## APPLICATIONS

- For high speed switching applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	500	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current (DC)		7	A
$I_{CM}$	Collector current-Peak		15	A
$I_B$	Base current		3	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.2A ; L=25mH	400			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.6A			1.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.6A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =500V; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =5V	15			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =3A ; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5 A ; V <sub>CE</sub> =10V		11		MHz

## Switching times

t <sub>on</sub>	Turn-on time	V <sub>CC</sub> =100V , I <sub>C</sub> =3A, I <sub>B1</sub> =-I <sub>B2</sub> =0.6A			1.0	μs
t <sub>s</sub>	Storage time				3.0	μs
t <sub>f</sub>	Fall time				1.0	μs

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PACKAGE OUTLINE

